

1	Kyung Min Lee ★ Seoul National University, Republic of Korea	180 - Investigating Intermediate-State-Induced Write Error Rate Degradation in Magnetic Tunnel Junctions via Domain-Level Electrical Analysis
2	Shisong Luo ★ Rice University, United States	174 - GaN p-Channel MOSFET with ALD Ga ₂ O ₃ Gate Dielectric Featuring a High BFOM (0.43 MW/cm ²) and over 200 V Blocking Capability
3	Ashutosh Krishna Amaram ★ University of Illinois Chicago, United States	231 - Atomistic Insights into the Switching Mechanism and the Origin of Device-to-Device Variability in Ta-HfO ₂ -Pt based Memristive Device
4	Xucheng Yang ★ NC State University, United States	178 - Experimental Design Parameter Exploration of Ultra-Low Threshold III-V/Si Quantum Dot Microring Lasers
5	Jianming Huang ★ Southern University of Science and Technology, China	305 - Confining mobile ions for 40x transient NDR in ITO/HfO ₂ FETs with incomplete top gate metal coverage
6	Shubham Babbar ★ Ben-Gurion University of the Negev, Israel	88 - Multiple biomarkers detection under a single drop of physiological solution using a field-effect transistor
7	Sanjeev Khare ★ Purdue University, United States	264 - Octupole Transfer Torque and Spin-Orbit Torque Driven Oscillations and Switching in Cubic Chiral All-AFM Devices
8	Debaditya Bhattacharya ★ Cornell University, United States	170 - High-current ultrawide-bandgap AlGa _N pin diodes with low on-resistance and UVC emission
9	Alexander Karl ★ TU Wien, Austria	125 - Physics-Based Modeling of Reliability, Stability, and Leakage in 2D MOSFETs
10	Akshey Dhar ★ Cornell University, United States	261 - Enhancement Mode Operation of AlN XHEMTs
11	Kyota Mikami Kyoto University, Japan	164 - Mobility Improvement in SiC MOSFETs by Shallow Counter Doping
12	Krishna Rudrapal University of Stuttgart, Germany	187 - Low-Voltage Forming-Free, Abrupt, and Gradual Resistive Switching in Surface-Modified IGZO Memristors
13	Myungsoo Kim UNIST, Republic of Korea	173 - Low-Noise and Hysteresis-Free MoS ₂ Transistors Enabled by High-k Single-Crystalline Rare-Earth Oxychloride Dielectrics
14	Alireza Moazzeni Wayne State University, United States	253 - Identification of Cycle-to-Cycle Switching Regimes in Filamentary TaO _x RRAM using Time Series Analysis
15	Soren Schafer University of Stuttgart, Germany	193 - Aging of Unencapsulated Te Transistors in Ambient Air and Comparison of Annealing Conditions
16	Sara Ghazvini University of Texas at Dallas, United States	147 - High-Speed, Low-Voltage Ge/Si APDs Optimized with Bayesian Optimization and TCAD for CMOS Integration

17	Haixin Zhao <i>University of Delaware, United States</i>	185 - Phase Reconfigurability-enhanced Metasurface Image Compression with an Integrated Photonic Encoder
18	Showmik Singha <i>University of Missouri-Columbia, United States</i>	139 - Machine Learning Enabled Parameter Extraction of beta-Ga2O3 MOSFETs
19	VENKATESWARLU GADDAM <i>University of Florida, United States</i>	246 - Hybrid Epitaxial/Textured AlN Seed Layer Impact on Ferroelectric Al0.7Sc0.3N Memory Devices
20	Xin Su <i>Penn State University, United States</i>	66 - Noise and Drift Models for Electrochemical Memory (ECRAM)
21	Md Rahatul Islam Uday <i>University of Tennessee Knoxville, United States</i>	190 - High Temperature 1T1R Memory Using Ferroelectric Diode and GaN Transistor
22	Dimitrios Spithouris <i>Forschungszentrum Juelich, Germany</i>	219 - Volatile amorphous SrTiO3-based memristive devices with tunable temporal dynamics for event-based sensing
23	Md Sazzadur Rahman <i>Duke University, United States</i>	310 - Unconventional BTI in ITO FETs: Thickness-Tuned Temperature-Induced Polarity Reversal
24	Asmita Thool <i>IIT Madras, India</i>	286 - Non-filamentary resistance switching in CVD-MoS2 memristive devices
25	Katherina Loske <i>University of Florida, United States</i>	128 - 13.5 kV NiO/beta-Ga2O3 Heterojunction Rectifiers on 4-Inch Wafers with Dielectric-Assisted Field-Plate Edge Termination
26	Arka Chakraborty <i>IIT Kanpur, India</i>	203 - Cryogenic Compatible Temperature Responsive Model of Vertical InAs/InGaAs GAA Nanowire Ferroelectric FET for Neuromorphic Applications
27	ARPAN GHOSH <i>Penn State University, United States</i>	67 - Light-induced giant random telegraph noise in CuScP2S6/MoS2 heterostructures and their use in noise resilience image inference
28	Nihal Raut <i>IIT Bombay, India</i>	201 - Self-Adaptive Hybrid CMOS-FeCAP Image Sensor for Dynamic Range Enhancement
29	Fevronia Andreou <i>Texas A&M University, United States</i>	202 - Performance and Energy Efficiency Enhancement in HfO2-Based ReRAMs via Mo Doping
30	Jianan Song <i>Penn State University, United States</i>	71 - Study of leakage current in GaN junction field-effect transistor under heavy ion radiation
31	Jianming Huang <i>Southern University of Science and Technology, China</i>	307 - Mobile-ion-induced transient NDR in emerging FETs: Optimization insights and figures of merit via compact modeling
32	Shicheng Su <i>KAUST, Saudi Arabia</i>	61 - In-sensor learning via microfluidic neuromorphic charge-trapping memory
33	Shayan Parhizkar <i>AMO GmbH / RWTH Aachen University, Germany</i>	114 - Wafer-Scale Waveguide-Integrated Graphene-based Optoelectronic Mixers

34	Sooyeol Bae <i>KAIST, Republic of Korea</i>	57 - A Physics-Based Analytical Threshold Voltage Model of Oxide Semiconductor Governed by Depletion Width
35	Mayuri Sritharan <i>University of Waterloo, Canada</i>	189 - Emulating Neuron and Synaptic Functions through Antiferroelectric Tunnel Junctions: A Novel Dynamic Simulation Approach
36	MD YASIR BASHIR <i>IIT Kanpur, India</i>	197 - Highly Scalable Multi-Bit Monolithic Stackable 3D Dynamic Random-Access Memory Cell
37	Nolan Hendricks <i>Air Force Research Laboratory, United States</i>	186 - DC and RF Performance of GaN MISHEMTs with High-kappa AlTiO Nanolaminate Gate Dielectric
38	Cesely Smith <i>Carnegie Mellon University, United States</i>	162 - Contact Engineering of Foundry n-Type CNFETs with Al Contacts
39	Parthiban Santhanam <i>UCLA, United States</i>	252 - Chip-Scale Optoelectronic Voltage Boost Converters
40	Sung-Kun Park <i>SK hynix, Republic of Korea</i>	116 - Evolution of single-poly embedded NVM for low-density code storage EEPROM
41	Md Arifuzzaman Faisal <i>University of Michigan, United States</i>	138 - Exact field Solution of Contact Resistance in Anisotropic 2D Transistors with Experimental Benchmarking
42	Atul Sachan <i>IIT Bombay, India</i>	233 - Field-Assisted Charge Trapping in ALPO-IGZTO TFTs Enabling High Endurance and Long-Term Retention Without Tunneling and Blocking Layer
43	Jiahui Yang <i>Duke University, United States</i>	315 - Record Switching Speed of 100 ns in Interfacial Memristors with High Uniformity
44	Ram Munde <i>Purdue University, United States</i>	268 - Nanoscale Thermal Resistance Mapping of Nanocrystalline Cu Thin Films Using Scanning Thermal Microscopy with Hertzian Contact Geometric Correction
45	Dawei Wang <i>Arizona State University, United States</i>	84 - GaN Vertical Trench MOSFET Using Stepped Power Slanted RIE Polish
46	Michiel van Setten <i>imec, Belgium</i>	306 - Atomistic modeling of fluorine doping in IGZO
47	Jeelka Solanki <i>University at Albany, United States</i>	165 - In-Memory Image Processing Using 65nm CMOS-integrated 1T-1R RRAM Arrays
48	Abdul Momin Syed <i>KAUST, Saudi Arabia</i>	168 - A Highly Stable Multimodal Perovskite Heterojunction Memristor Enabling In-Memory Perception
49	Xiaojun Zheng <i>Penn State University, United States</i>	229 - High Temperature Switching in ALD-Grown Ferroelectric AlN Thin-Film Transistors with ZnO Channel
50	Riya Rajpurohit <i>University of Virginia, United States</i>	302 - Atom to System Model for a Superconducting Non-volatile Memory Device
51	Abhrajit Roy <i>IIT Bombay, India</i>	200 - Solution-Processed Ti-Pt/NiO/Ag Non-Volatile Devices as Synapses and Neurons in Analog Spiking Neural Network Hardware